



## Product/Process Change Notice - PCN 23\_0094 Rev. -

Analog Devices, Inc. One Analog Way, Wilmington, MA 01887, USA

This notice is to inform you of a change that will be made to certain ADI products (see Appendix A) that you may have purchased in the last 2 years. **Any inquiries or requests with this PCN (additional data or samples) must be sent to ADI within 30 days of publication date.** ADI contact information is listed below.

<b>PCN Title:</b>	LTM4637 and LTM4639 - FET and SUBSTRATE (BGA Package ONLY)
<b>Publication Date:</b>	03-Jul-2023
<b>Effectivity Date:</b>	05-Oct-2023 <i>(the earliest date that a customer could expect to receive changed material)</i>
<b>Revision Description:</b>	Initial Release

### Description Of Change:

- Analog Devices, Inc. qualified an alternate FET for use in the assembly of LTM4637 and LTM4639.
- Substrate Design revised and qualified for alternate FET.

### Reason For Change:

- Current FET facing End of Life.
- Substrate Design revision to accommodate new FET footprint.

### Impact of the change (positive or negative) on fit, form, function & reliability:

The change is transparent in customer applications since there is no change in form, fit, function, quality or reliability of the products. The product datasheet is unchanged.

### Product Identification *(this section will describe how to identify the changed material)*

Production shipment of the product incorporating the new material will begin no sooner than the effective date.

### Summary of Supporting Information:

Qualification performed per Industry Standard Test Methods. See attached Qualification result.

### Supporting Documents

**Attachment 1: Type:** Qualification Results Summary

[ADI\\_PCN\\_23\\_0094\\_Rev\\_-\\_RQR11052A.pdf...](#)

Note: If applicable, the device material declaration will be updated due to material change.

### ADI Contact Information:

For questions on this PCN, please send an email to the regional contacts below or contact your local ADI sales representatives.

<b>Americas:</b>	<b>Europe:</b>	<b>Japan:</b>	<b>Rest of Asia:</b>
PCN_Americas@analog.com	PCN_Europe@analog.com	PCN_Japan@analog.com	PCN_ROA@analog.com

## Appendix A - Affected ADI Models:

### Added Parts On This Revision - Product Family / Model Number (6)

LTM4637 / LTM4637EY#PBF

LTM4637 / LTM4637Y

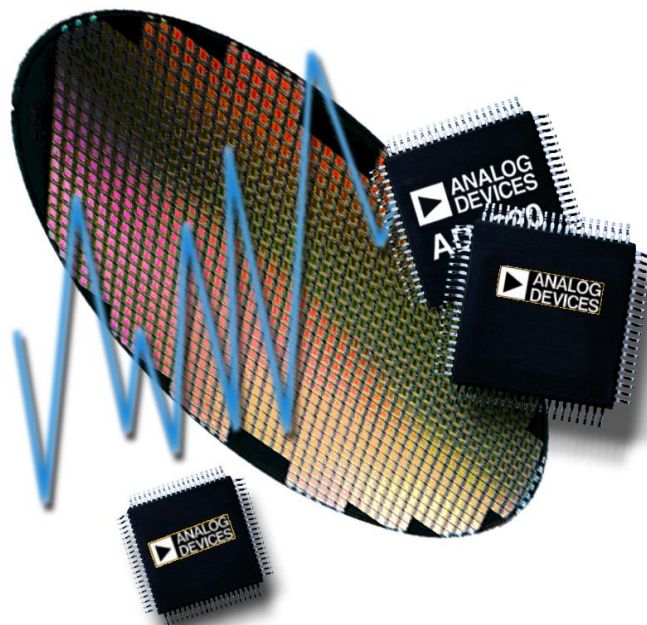
LTM4637 / LTM4637Y#PBF

LTM4639 / LTM4639EY#PBF

LTM4639 / LTM4639Y

LTM4639 / LTM4639Y#PBF

Appendix B - Revision History:			
Rev	Publish Date	Effectivity Date	Rev Description
Rev. -	03-Jul-2023	05-Oct-2023	Initial Release



# ***Reliability Report***

**Report Title:** LTM4637 and LTM4639 Material Set  
Change Qualification

**Report Number:** 19167

**Revision:** A

**Date:** 10 March 2023

## Summary

This report documents the successful completion of the reliability qualification requirements for the release of the LTM4637, LTM4639 product in 133-CSP\_BGA package. The LTM4637 and LTM4639 are 20A DC/DC uModule step-down regulators. This report is to qualify them with PMU9163 Alpha&Omega AONX36322 MOSFET.

## Die/Fab Product Characteristics

**Table 1: Die/Fab Product Characteristics**

Product Characteristics	Product(s) to be qualified	Product(s) to be qualified	Product(s) to be qualified	Product(s) to be qualified
Generic/Root Part #	LTM4639	LTM4639	LTM4637	LTM4637
Die Id	3855	6700-3	3855	6700-3
Die Size (mm)	1.78 x 1.78	1.47 x 0.81	1.78 x 1.78	1.47 x 0.81
Wafer Fabrication Site	ADI Milpitas	ADI Camas	ADI Milpitas	ADI Camas
Wafer Fabrication Process	0.6µm BiCMOS	4um Bipolar	0.6µm BiCMOS	4um Bipolar
Die Substrate	Si	Si	Si	Si
Metallization / # Layers	AlCu / 2	AlSiCu / 1	AlCu / 2	AlSiCu / 1
Polyimide	No	No	No	No
Passivation	doped-oxide/SiN	undoped-oxide/SiN	doped-oxide/SiN	undoped-oxide/SiN

## Package/Assembly Product Characteristics

**Table 2: Package/Assembly Product Characteristics - 133-CSP\_BGA at ADI Penang**

Product Characteristics	Product(s) to be qualified	
Generic/Root Part #	LTM4637	LTM4639
Package	133-CSP_BGA	133-CSP_BGA
Body Size (mm)	15.00 x 15.00 x 4.92	15.00 x 15.00 x 4.92
Assembly Location	ADPG	ADPG
MSL/Peak Reflow Temperature(°C)	4 / 245	4 / 245
Mold Compound	Sumitomo G311E	Sumitomo G311E
Die Attach	Multicore 95Sn/5Sb	Multicore 95Sn/5Sb
Substrate Material	BT Resin	BT Resin
Lead Finish	96.5Sn_3.0Ag_0.5Cu	96.5Sn_3.0Ag_0.5Cu
Wire Bond Material/Diameter (mils)	Gold / 1.00	Gold / 1.00

## QMCL

PID P/N	Description	Vendor, Vendor P/N
PMU9163	MOSFET	Alpha&Omega, AONX36322

## Reliability Test Results

**Table 3: Reliability Test Results – LTM4637 and LTM4639**

Test Name	Spec	Conditions	Generic/Root Part #	Lot #	Fail/SS
High Temperature Operating Life (HTOL)	JESD22-A108	125°C<Tj<135°C, Biased, 1,000 Hours	LTM4639	Q19167.6HTOL	0/77
			LTM4637	Q19167.5HTOL	0/77
Temperature Cycling (TC) <sup>1</sup>	JESD22-A104	-55°C/+125°C, 1,000 Cycles	LTM4637	Q19167.1TC	0/77
			LTM4639	Q19167.2TC	0/77
Thermal Shock (TS) <sup>1</sup>	JESD22-A106	-55°C/+125°C, 1,000 Cycles	LTM4637	Q19167.1TS	0/77
			LTM4639	Q19167.2TS	0/77
Unbiased HAST (UHST) <sup>1</sup>	JESD22-A118	110C 85%RH 17.7 psia, 264 Hours	LTM4637	Q19167.1UHAST	0/77
			LTM4639	Q19167.2UHAST	0/77

<sup>1</sup> These samples were subjected to preconditioning (per J-STD-020 Level 3) prior to the start of the stress test. Level 3 preconditioning consists of the following: Bake: 48 hrs @ 125°C, Unbiased Soak: 192 hrs @ 30°C, 60%RH, Reflow: 3 passes through an oven with a peak temperature of 245°C.

## Approvals

Reliability Engineer: Yi Ning